



Schottky Diodes



- High frequency operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 ℃

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

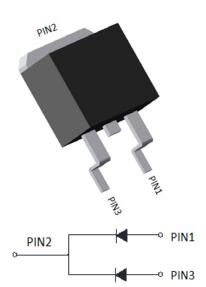
Mechanical Data

• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102
• Polarity: As marked



■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBRBL1060CT
Device marking code			MBRBL1060CT
Repetitive Peak Reverse Voltage	VRRM	٧	60
Average Rectified Output Current @60Hz sine wave, R-load, T _C =138°C	Ю	Α	10
Surge(Non-repetitive)Forward Current @60H _Z half sine-wave, 1 cycle, T _a =25℃	IFSM	Α	100
Current Squared Time @1ms≤t≤8.3ms Tj=25°C	l²t	A ² s	41
Storage Temperature	T _{stg}	°C	-55 ~ +150
Junction Temperature	Tj	°	-55 ~ +150

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRBL1060CT
Maximum instantaneous forward voltage drop per diode	VFM	٧	IFM=5.0A	0.6
Maximum DC reverse current at rated DC blocking voltage per diode	IRRM1	mA	VRM=VRRM T _a =25°C	0.2
	IRRM2		VRM=VRRM T _a =100°C	20

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS

MBRBL1060CT

Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARA	AMETER	SYMBOL	UNIT	MBRBL1060CT
Thermal Resistance	Between junction and case	R ₀ J-C	°CW	2.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MDDDI 40000T	Approximate 1.43	50	2000	8000	Tube
MBRBL1060CT	Approximate 1.43	1000	2000	10000	Reel

■Characteristics (Typical)

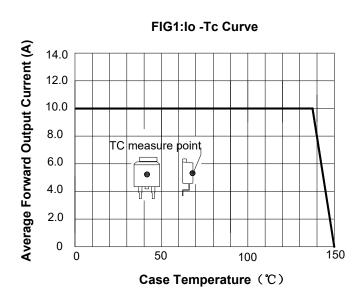
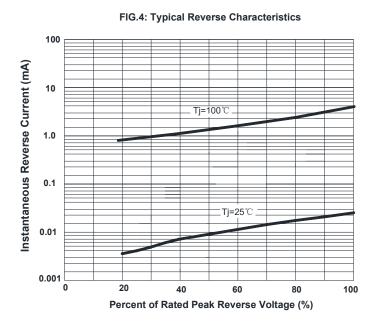


FIG2:Surge Forward Current Capability 140 Peak Forward Surge Current (A) 120 100 8.3ms Single Half Sine-Wave 80 JEDEC Method 60 20 2 5 20 50 10 100

Number of Cycles

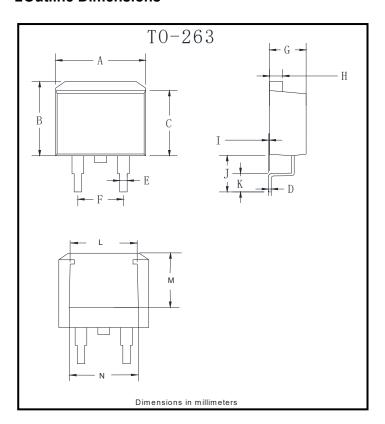
50 Instantaneous Forward Current (A) 20 10 5.0 1.0 0.5 0.2 Ta=25℃ 0.1 0 0.2 0.5 0.6 0.7 0.8 0.9 1.0 Instantaneous Forward Voltage (V)

FIG3: Forward Voltage



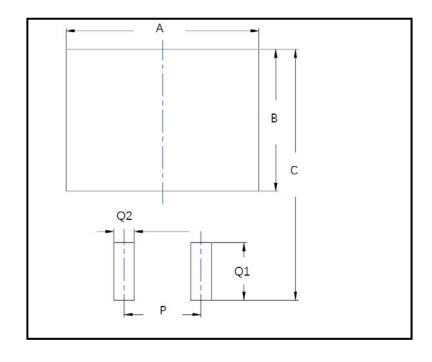


■Outline Dimensions



TO-263				
Dim	Min	Max		
Α	9.5	11.5		
В	9.7	10.5		
С	8.4	9.0		
D	0.28	0.64		
Е	0.68	0.94		
F	4.55	5.6		
G	4.04	5.10		
Н	1.14	1.4		
I	0	0.2		
J	4.9	6.05		
K	1.79	2.79		
L	7.3	7.9		
М	6.2	6.8		
N	7.6	8.2		

■Suggested Pad Layout



Dim	Millimeters
Α	12.7
В	9.4
С	16.6
Р	5.08
Q1	3.8
Q2	1.35



MBRBL1060CT

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